

ROHS COMPLIANT

Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

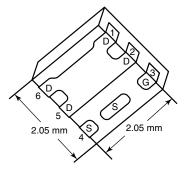
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω) I_D (A)		Q _g (Тур)		
- 20	0.035 at V _{GS} = - 4.5 V	- 12 ^a	15 nC		
	0.051 at V _{GS} = - 2.5 V	- 12 ^a	13110		

FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance

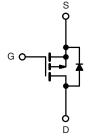
APPLICATIONS

Load Switch, PA Switch and Battery Switch for Portable
Devices



PowerPAK SC-70-6L-Single

Marking Code



Ordering Information: SiA415DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise note	ed		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 20	v	
Gate-Source Voltage		V _{GS}	± 12	- v	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C T _C = 70 °C	I _D	- 12 ^a - 12 ^a	_	
	T _A = 25 °C T _A = 70 °C	·D	- 8.4 ^{b, c} - 6.7 ^{b, c}	А	
Pulsed Drain Current		I _{DM}	- 30		
Continuous Source-Drain Diode Current	T _C = 25 °C T _A = 25 °C	I _S	- 12 ^a - 2.9 ^{b, c}	\neg	
Maximum Power Dissipation	T _C = 25 °C T _C = 70 °C	P _D	19 12	w	
	T _A = 25 °C T _A = 70 °C		3.5 ^{b, c} 2.2 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5		

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 80 °C/W.

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static				<u> </u>			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050A		- 20		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μΑ		3.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.6		- 1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
7		$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1		
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 4.5 V	- 20			А	
		V _{GS} = - 4.5 V, I _D = - 5.6 A		0.029	0.035	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2 A		0.042	0.051		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 5.6 A		20		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1250		pF	
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		250			
Reverse Transfer Capacitance	C _{rss}			190			
		$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8.4 \text{ A}$		31	47	nC	
Total Gate Charge	Qg			15	23		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 8.4 A		2.8			
Gate-Drain Charge	Q _{gd}			5			
Gate Resistance	Rg	f = 1 MHz		7		Ω	
Turn-On Delay Time	t _{d(on)}			25	40		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1.5 Ω		50	75	-	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 6.7 A, V_GEN = - 4.5 V, R_g = 1 Ω		40	60		
Fall Time	t _f			20	30		
Turn-On Delay Time	t _{d(on)}			10	15	- ns - -	
Rise Time	t _r	V_{DD} = - 10 V, R _L = 1.5 Ω		10	15		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 6.7 A, V_GEN = - 10 V, R_g = 1 Ω		45	70		
Fall Time	t _f			12	20		
Drain-Source Body Diode Characterist	ics			I			
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			- 12	۸	
Pulse Diode Forward Current	I _{SM}				30	A	
Body Diode Voltage	V _{SD}	I _S = - 6.7 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	0		35	55	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			21	35	nC	
Reverse Recovery Fall Time	ta	· I _F = - 6.7 A, di/dt = 100 A/μs, T _J = 25 °C		12			
Reverse Recovery Rise Time	t _b	1 1		23		ns	

Notes:

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





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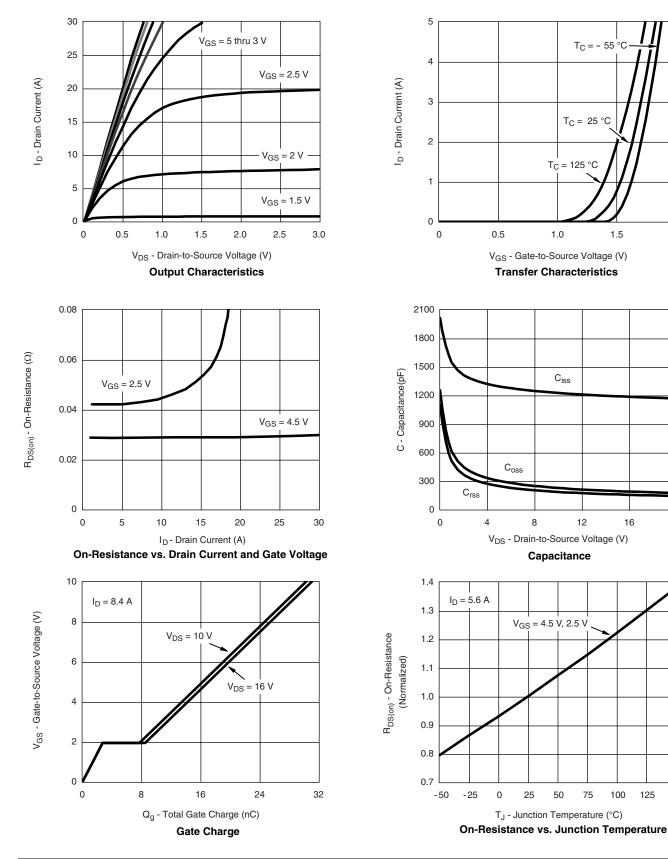
1.5

16

20

2.0

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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125

150

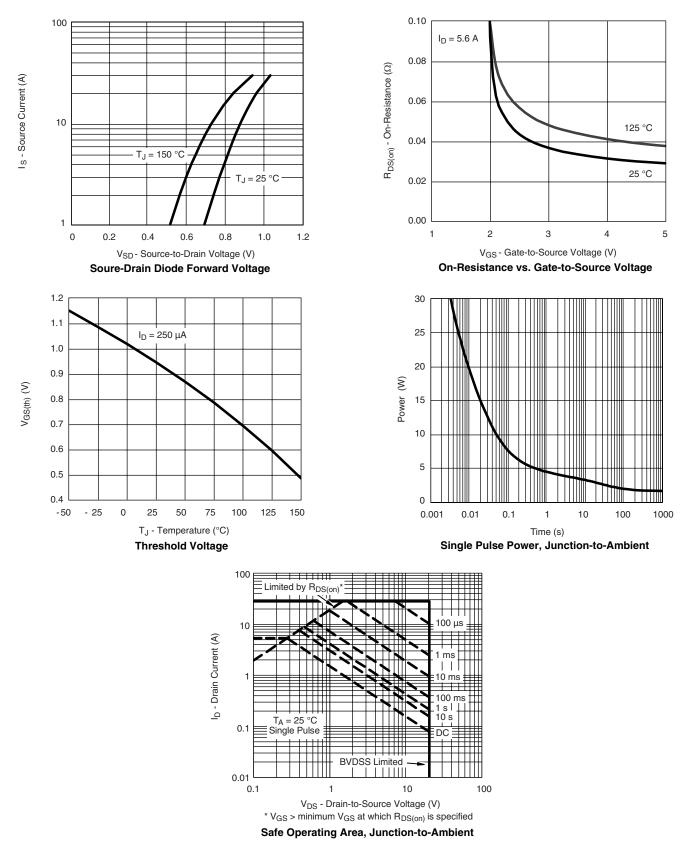
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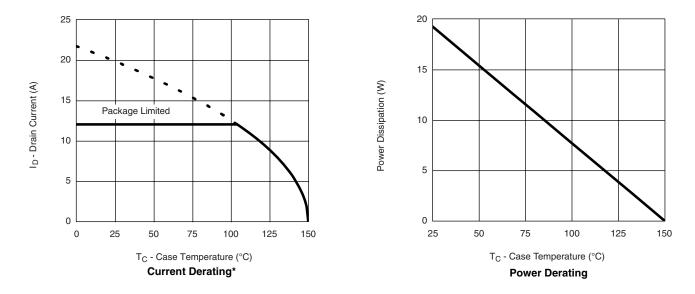






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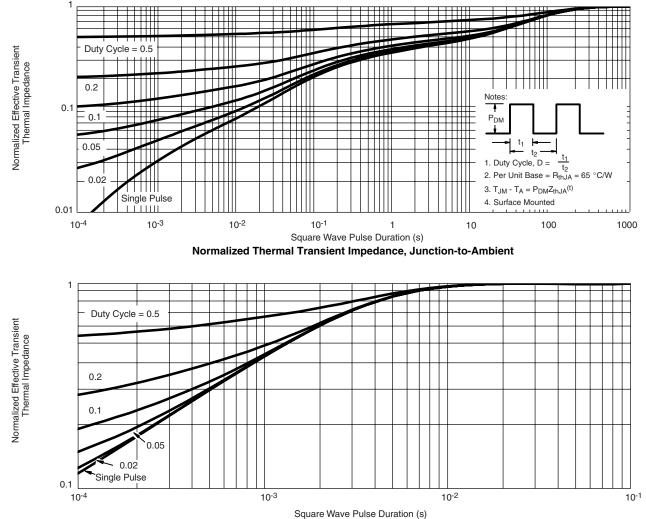
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?69512.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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